

**isc Silicon PNP Power Transistor**

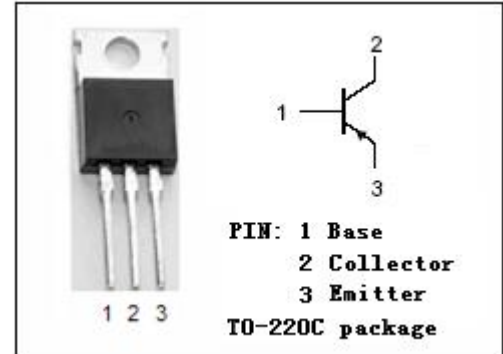
**2SB782**

**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -60V(\text{Min})$
- Good Linearity of  $h_{FE}$
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

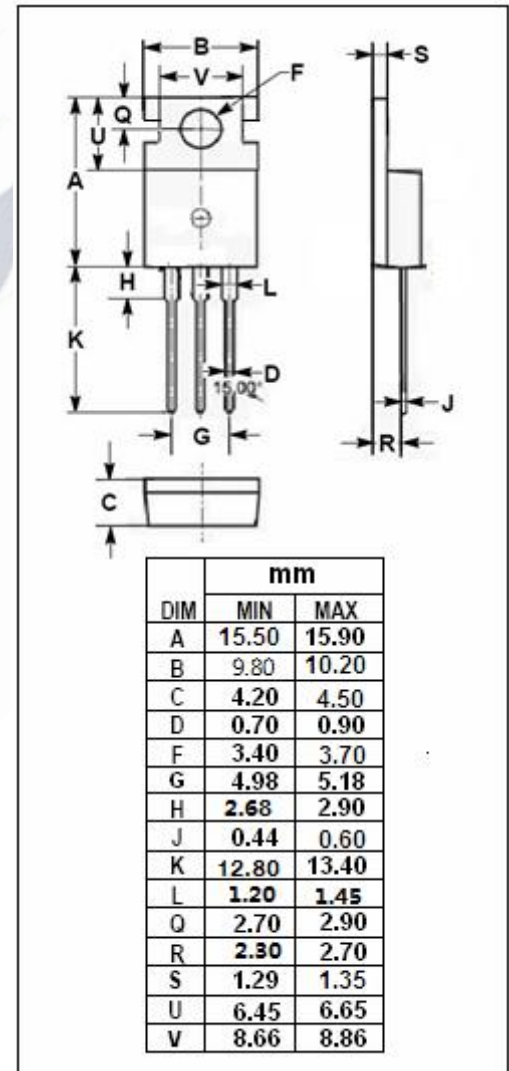
**APPLICATIONS**

- Designed for use in general purpose power amplifier and switching applications



**ABSOLUTE MAXIMUM RATINGS(Ta=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-4	A
$I_{CM}$	Collector Current-Peak	-6	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	30	W
$T_J$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature Range	-55~150	°C



**isc Silicon PNP Power Transistor****2SB782****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA ; I <sub>B</sub> = 0	-60			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.4A			-1.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -0.5A ; V <sub>CE</sub> = -5V			-1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -60V ; I <sub>E</sub> = 0			-100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-10	μ A
h <sub>FE1</sub>	DC Current Gain	I <sub>C</sub> = -0.5A ; V <sub>CE</sub> = -5V	60		320	
h <sub>FE2</sub>	DC Current Gain	I <sub>C</sub> = -4A ; V <sub>CE</sub> = -5V	10			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> = -10V	5			MHz